

CLAIM AMENDMENTS

IN THE CLAIMS

This listing of the claims will replace all prior versions, and listing, of claims in the application or previous response to office action:

1. **(Currently Amended)** A power semiconductor module comprising a plurality of semiconductor components situated on a substrate, wherein

- the substrate is divided into a plurality of separate substrate regions and
- one or a plurality of connecting regions are ~~situated~~**arranged in** between adjacent substrate regions, wherein said connecting region are designed **such to prevent a deformation** ~~that a movement~~ of one substrate region[s] ~~does not translate to continue~~ to an adjacent substrate region.

2. **(Previously Presented)** The power semiconductor module as claimed in claim 1, wherein

- the connecting regions are formed by recesses in a module housing enclosing said substrate regions.

3. **(Original)** The power semiconductor module as claimed in claim 2, wherein

- the material recesses are slotted.

4. **(Original)** The power semiconductor module as claimed in claim 1, wherein

- the substrate is a ceramic.

5. **(Original)** The power semiconductor module as claimed in claim 2, wherein

- the substrate is a ceramic.

6. **(Canceled)**

7. **(Canceled)**

8. (Previously Presented) The power semiconductor module as claimed in claim 2, wherein

- the module housing, at least in the regions of the substrate regions, is such that it acts on the substrate regions with a spring force.

9. (Previously Presented) The power semiconductor module as claimed in claim 3, wherein

- the module housing, at least in the regions of the substrate regions, is such that it acts on the substrate regions with a spring force.

10. (Canceled)

11. (Original) The power semiconductor module as claimed in claim 5, wherein

- the housing, at least in the regions of the substrate regions, is such that it acts on the substrate regions with a spring force.

12. (Original) The power semiconductor module as claimed in claim 6, wherein

- the housing, at least in the regions of the substrate regions, is such that it acts on the substrate regions with a spring force.

13. (Original) The power semiconductor module as claimed in claim 1, wherein

- the power semiconductor module has a housing, which, in the region between the substrate regions, has action points for a mechanical pressure application of the connecting regions, and
- the housing applies pressure to the individual substrate regions.

14. (Currently Amended) A power semiconductor module comprising

- a plurality of substrate elements having top and bottom surface, each substrate element comprising a semiconductor component arranged on the top surface of a substrate element;
- one or a plurality of connecting regions arranged in between adjacent substrate regions to form a continuous bottom surface, wherein said connecting region are designed to prevent a deformation such that a movement of one substrate region[s] ~~does not translate to continue~~ to an adjacent substrate region.

15. (Previously Presented) The power semiconductor module as claimed in claim 14, further comprising a module housing enclosing said plurality of substrate elements.

16. (Previously Presented) The power semiconductor module as claimed in claim 15, wherein

- the connecting regions are formed by recesses in the module housing.

17. (Previously Presented) The power semiconductor module as claimed in claim 16, wherein

- the material recesses are slotted.

18. (Previously Presented) The power semiconductor module as claimed in claim 14, wherein

- the substrate is a ceramic.

19. (Previously Presented) The power semiconductor module as claimed in claim 15, wherein

- the module housing, at least in the regions of the substrate elements, is such that it acts on the substrate elements with a spring force.

20. **(Currently Amended)** The power semiconductor module as claimed in claim 14, further comprising

- a heat sink having a flat surface, wherein the continuous bottom surface of the plurality of substrate elements and said plurality of connecting regions are arranged on said flat surface.

21. **(Previously Presented)** The power semiconductor module as claimed in claim 15, wherein

- the module housing in the region between the substrate elements comprises action points for a mechanical pressure application of the connecting regions, and
- the housing applies pressure to the individual substrate elements.

22. **(NEW)** The power semiconductor module as claimed in claim 1, further comprising

- a heat sink having a flat surface, wherein the continuous bottom surface of the plurality of substrate elements and said plurality of connecting regions are arranged on said flat surface.

23. **(NEW)** A power semiconductor module comprising:

- a heat sink having a flat surface,
- a plurality of substrates arranged on the flat surface of the heat sink;
- a plurality of semiconductor components arranged on the substrates,
- one or a plurality of connecting regions arranged on the flat surface of the heat sink between adjacent substrate regions, wherein the connecting regions are designed to prevent a deformation of one substrate region to continue to an adjacent substrate region.